

ABSTRACT OF THE DISCLOSURE

A method of fabricating a semiconductor package is disclosed in which a first Ni-Au plating is formed on a bonding pad for connection with a semiconductor chip, without a mechanical process or a masking operation. The method applies a copper plating on a through bore and the bonding pad, where the copper plated layer formed on the bonding pad is selectively removed, and then a second Ni-Au plating is formed on the bonding pad and a ball pad.